

STPS10L60D/FP

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

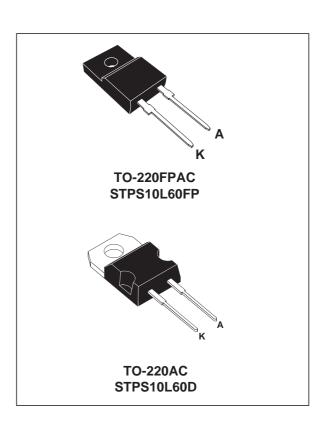
I _{F(AV)}	10 A
V _{RRM}	60 V
Tj (max)	150°C
V _F (max)	0.56 V

FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP
- NEGLIGIBLE SWITCHING LOSSES
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Schottky rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters. Packaged in TO-220AC,TO-220FPAC this device is intended for use in DC/DC chargers.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			60	V
I _{F(RMS)}	RMS forward current			30	А
I _{F(AV)}	Average forward current	TO-220AC	$Tc = 140^{\circ}C \ \delta = 0.5$	10	А
		TO-220FPAC	$Tc = 120^{\circ}C \delta = 0.5$		
I _{FSM}	Surge non repetitive forward	220	Α		
I _{RRM}	Repetitive peak reverse current tp = 2 µs square F=1kHz			1	Α
P _{ARM}	Repetitive peak avalanche power tp = 1µs Tj = 25°C			5800	W
T _{stg}	Storage temperature range			- 65 to + 175	°C
Tj	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs

^{* :} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ thermal runaway condition for a diode on its own heatsink

July 2003 - Ed: 4B

STPS10L60D/FP

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	TO-220AC	1.6	°C/W
		TO-220FPAC	4	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage current	Tj = 25°C	$V_R = V_{RRM}$			350	μΑ
	_	Tj = 125°C			65	95	mΑ
V _F *	Forward voltage drop	Tj = 25°C	I _F = 10 A			0.6	V
		Tj = 125°C	I _F = 10 A		0.48	0.56	
		Tj = 25°C	I _F = 20 A			0.74	
		Tj = 125°C	I _F = 20 A		0.62	0.7	

Pulse test: * tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation :

 $P = 0.42 \times I_{F(AV)} + 0.014 I_{F}^{2}(RMS)$

Fig. 1: Average forward power dissipation versus average forward current.

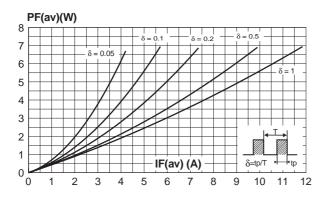


Fig. 3: Normalized avalanche power derating versus pulse duration.

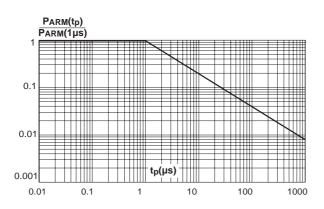


Fig. 2: Average forward current versus ambient temperature($\delta = 0.5$).

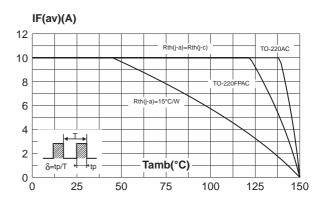


Fig. 4: Normalized avalanche power derating versus junction temperature.

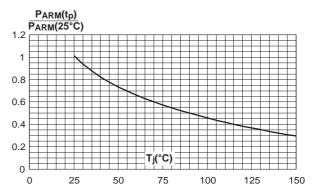


Fig. 5-1: Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220AC).

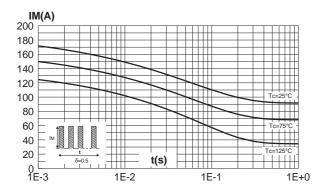


Fig. 6-1: Relative variation of thermal impedance junction to lead versus pulse duration (TO-220AC).

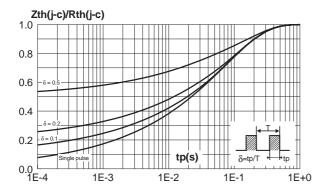


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

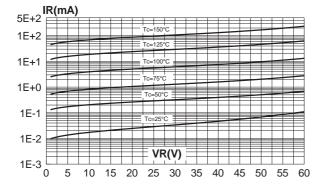


Fig. 5-2: Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220FPAC).

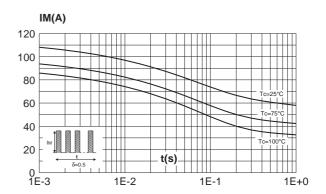


Fig. 6-2: Relative variation of thermal impedance junction to lead versus pulse duration (TO-220FPAC).

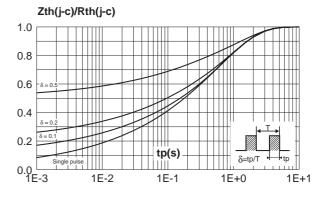
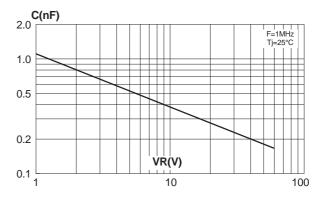
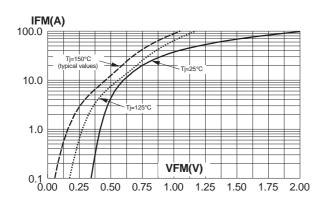


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).



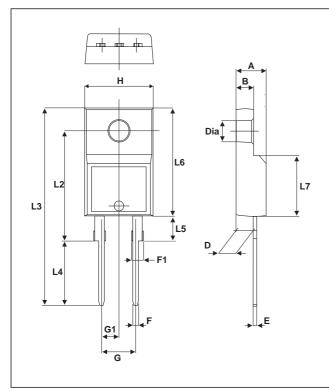
3/5

Fig. 9: Forward voltage drop versus forward current (low level, maximum values).



PACKAGE MECHANICAL DATA

TO-220FPAC



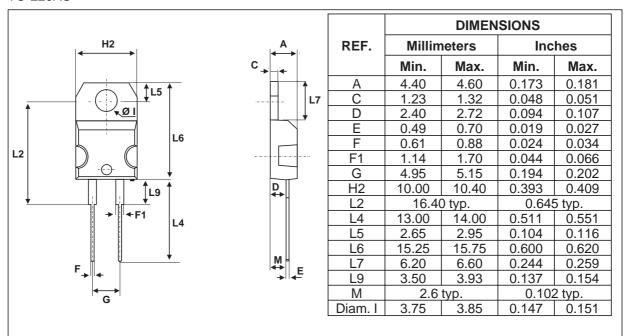
REF.	DIMENSIONS				
	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.4	4.6	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.5	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1	0.030	0.039	
F1	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.4	2.7	0.094	0.106	
Н	10	10.4	0.393	0.409	
L2	16	Гур.	0.63	Тур.	
L3	28.6	30.6	1.126	1.205	
L4	9.8	10.6	0.386	0.417	
L5	2.9	3.6	0.114	0.142	
L6	15.9	16.4	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia.	3.00	3.20	0.118	0.126	

57

STPS10L60D/FP

PACKAGE MECHANICAL DATA

TO-220AC



COOLING METHOD : C

■ RECOMMENDED TORQUE VALUE: 0.8M.N

■ MAXIMUM TORQUE VALUE: 1.0M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS10L60D	STPS10L60D	TO-220AC	1.86g	50	Tube
STPS10L60FP	STPS10L60FP	TO-220FPAC	1.9g	50	Tube

■ EPOXY MEETS UL94,V0

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